WHAT IS CLAIMED IS:

1. A deposition apparatus comprising:

a plasma generator configured to generate a plasma by arc discharge; and

a deposition unit configured to form a film on a member by the plasma generated by the plasma generator,

wherein the plasma generator includes:

a target holder configured to hold a target and apply a negative potential to the target;

an anode to which a positive potential is applied; and

a capture configured to capture droplets from the target, and

wherein the anode has an opening, the capture is arranged in the opening, and the anode is arranged below the target.

2. The deposition apparatus according to claim 1, wherein the anode has a first cylindrical portion, and the capture includes a second cylindrical portion arranged inside the first cylindrical portion to let the plasma pass, and a flange portion extending from the second cylindrical portion to an inner wall of the first cylindrical portion.

3. The deposition apparatus according to claim 1, further comprising:

a collection unit configured to collect droplets; and

a transport unit configured to transport droplets captured by the capture to the collection unit.

4. The deposition apparatus according to claim 3, wherein the plasma generator includes a discharge chamber, the target holder, the anode, and the capture are arranged in the discharge chamber, the collection unit is arranged outside the discharge chamber, and a valve is arranged between the discharge chamber and the collection unit.

5. The deposition apparatus according to claim 1, further comprising a guide configured to guide the plasma from the plasma generator to the deposition unit,

wherein the guiding unit includes a bent duct, and a plurality of baffles

arranged inside the duct to capture droplets, and

an opening dimension of a first baffle closest to the plasma generator among the plurality of baffles is equal to an opening dimension of the capture on a side of the guiding unit.

6. The deposition apparatus according to claim 2, further comprising a guiding unit configured to guide the plasma from the plasma generator to the deposition unit,

wherein the guiding unit includes a bent duct, and a plurality of baffles arranged inside the duct to capture droplets, and

an opening dimension of a first baffle closest to the plasma generator among the plurality of baffles is equal to an opening dimension of the second cylindrical portion on a side of the guiding unit.

7. The deposition apparatus according to claim 5, wherein the guiding unit includes a plurality of coils configured to generate a magnetic field for guiding the plasma, and the plurality of coils include a first coil formed in a portion of the duct between the capture and the first baffle.

8. The deposition apparatus according to claim 1, wherein the deposition unit is arranged in a position lower than the plasma generator.